

## The Effect of Nickel Intercalation on the Properties of $\text{In}_2\text{Se}_3$ Layered Crystals

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$\text{In}_2\text{Se}_3$  is a layered semiconductor with defective structure of tetrahedral bonding, where one-third of the sites is vacant and forms a screw array along the c axis.  $\text{In}_2\text{Se}_3$  layered crystals have been the subject of many investigations due to their peculiar electrical and optical properties, and their potential applications in various types of electronic and optoelectronic devices, phase-change random access memories, solid-state batteries, and solar cells, etc [1, 2].

$\text{In}_2\text{Se}_3$  single crystals were grown by the Bridgman modified method from a stoichiometric melt and characterized by a pronounced layered structure over the whole length of a sample. Intercalation of samples was performed by the electrochemical method in the course of the anodic reaction of intercalation in static gradient magnetic field of 50 A/m at the sample-electrolyte interface.  $\text{NiNO}_3$  saturated aqueous solution was used as the electrolyte. The concentration of embedded Ni (x) was calculated according to Faraday's law.

The influence of  $\text{Ni}^{2+}$  ions intercalation on properties of  $\text{In}_2\text{Se}_3$  monocrystals was investigated. It was shown that at the increase the concentration of  $\text{Ni}^{2+}$  ions the specific conductivity of  $\text{In}_2\text{Se}_3$  crystals tends to decline (Fig.). The basic samples of  $\text{In}_2\text{Se}_3$  single crystals are paramagnetic. It is found that  $\text{Ni}_x\text{In}_2\text{Se}_3$  samples have ferromagnetic properties at room temperature.

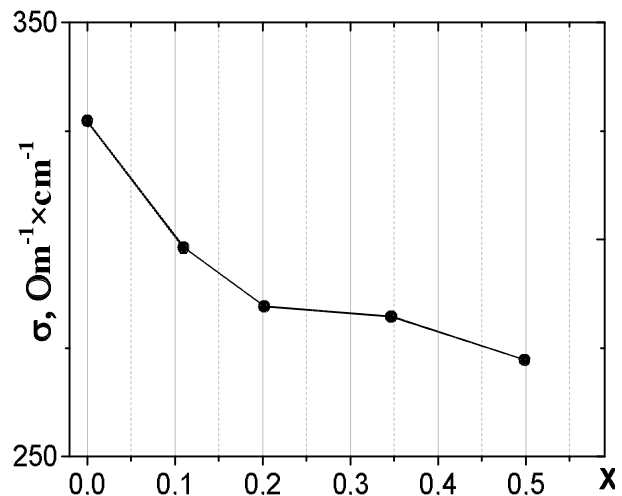


Fig. The dependence of  $\sigma_{\perp c}$  layer-parallel electrical conduction for  $\text{Ni}_x\text{In}_2\text{Se}_3$

1. Julien C., Eddrief M., Kambas K., Balkanski M. // Mater. Sci. Eng. B. 1996.V. 38. N 1. P. 1–8.
2. Bakhtinov, A.P., Boledzyuk, V.B., Kovalyuk, Z.D., Kudrinskii, Z.R., Litvin, O.S., and Shevchenko, A.D., Phys. Solid State, 2013, vol. 55, no. 6, pp. 1148–1155.